

AOS Semiconductor Product Reliability Report

AOZ18102DI-02 rev A

Plastic Encapsulated Device

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The AOS product reliability report summarizes the qualification results for AOZ18102DI-02 in DFN3X3-10L package. Accelerated environmental tests are performed on a specific sample size, samples are electrically tested before and after each stress time point. Review of final electrical test results confirm that AOZ18102DI-02 pass the AOS quality and reliability requirements. The released products will be categorized by its process family and routinely monitored for continuous improvement of product quality.

I. AOZ18102DI-02 Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Sample Size / Lots	Number of Failures	Reference Standard
HTOL	T _J = 125°C, V _{IN} = 20V	168 / 500 / 1000 hours	231 pcs (3 lots)	0	JESD22-A108
Preconditioning (Note A)	T _A = 85°C, RH = 85% + 3 cycle reflow @ 260°C (MSL 1)	168hours	924 pcs (3 lots)	0	JESD22-A113
HAST	T _A = 130°C, RH = 85%, P = 33.3psia, V _{IN} = 20V	96 hours	231 pcs (3 lots)	0	JESD22-A110
Temperature Cycle	T _A = -65°C to 150°C, air to air	500 / 1000 cycles	231 pcs (3 lots)	0	JESD22-A104
HTSL	T _A = 150°C	1000 hours	231 pcs (3 lots)	0	JESD22-A103
Autoclave	T _A = 121°C, RH = 100%, P = 29.7psia	96 hours	231 pcs	0	JESD22-A102
HTGB (MOSFET)	T _J = 150°C, V _{GS} = 5V	168 / 500 hours	231 (3 lots)	0	JESD22-A108
HTRB (MOSFET)	T _J = 150°C, V _{DS} = 18V	168 / 500 hours	231 (3 lots)	0	JESD22-A108

Note: The reliability data presents total of available generic data up to the published date.

Note A: MSL (Moisture Sensitivity Level) 1 based on J-STD-020

II. Reliability Evaluation

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the product technology. Failure Rate Determination is based on JEDEC Standard JESD 85.

FIT rate (failures per billion device hours): 2.559

MTTF = 390.8 million hrs=44614.16 years

Condition: V_o = 14V, T_o = 55°C, V_{s(IC)} = 20V, V_{s(MOSFET)} = 18V, T_{s(IC)} = 125°C and T_{s(MOSFET)} = 150°C

Accumulated Sample Size x Hours: MOSFET = 240000, IC = 1037320

The failure rate (λ) is calculated as follows:

$$\lambda = \chi^2[CL, (2f+2)] / 2 \times [1 / (SS \times t \times AF)]; \text{ [equation 1]} \quad \text{where} \quad \begin{array}{l} CL = \% \text{ of confidence level} \\ f = \text{number of failure} \\ SS = \text{sample size} \\ t = \text{stress time} \end{array}$$

Looking up the $\chi^2/2$ table for zero failure (burn-in) with 60% confidence, the value of $\chi^2[CL, (2f+2)] / 2$ is 0.92.

The Acceleration Factor (AF) is calculated from the following formula (both temperature and voltage acceleration factors are used in the final acceleration factor calculation) :

$$AF = AF_T \times AF_V = \exp[(E_a/k) \times (1/T_o - 1/T_s)] \times \exp[\beta (V_s - V_o)] \text{ where} \quad E_a = \text{activation energy}$$

k = Boltzmann constant
 T_o = operating T_J
 T_s = stress T_J
 V_s = stress voltage
 V_o = operating voltage
 β = voltage acceleration coefficient

Assuming typical operating environment, $V_o = 14V$, $T_o = 55^\circ C$, $E_a = 0.7eV$, $V_{s(IC)} = 20V$, $V_{s(MOSFET)} = 18V$, $T_{s(IC)} = 125^\circ C$ and $T_{s(MOSFET)} = 150^\circ C$, $\beta = 0.5$ (silicon defect)

$$AF(DriverIC) = \exp \left[\left(\frac{0.7}{8.617E - 5} \right) \cdot \left(\frac{1}{273 + 55} - \frac{1}{273 + 125} \right) \right] \cdot \exp[0.5 \cdot (20V - 14V)]$$

$$AF(MOSFET) = \exp \left[\left(\frac{0.7}{8.617E - 5} \right) \cdot \left(\frac{1}{273 + 55} - \frac{1}{273 + 150} \right) \right] \cdot \exp[0.5 \cdot (18V - 14V)]$$

Substituting the values in equation 1, we have

$$\lambda = 0.92 \cdot \frac{1}{Sample\ Size \cdot Stress\ Duration \cdot AF(MOSFET)} + \frac{1}{sample\ Size \cdot Stress\ Duration \cdot AF(DriverIC)} hr^{-1}$$

$\lambda = 2.559 \cdot 10^{-9} hr^{-1}$ or 2.559 FIT; MTTF = $(1/\lambda) = 390.8$ million hrs = 44614.16 years

The calculation shows failure rate is 2.559 FIT, MTTF is 390.8 million hours under typical operating conditions.

III. AOZ18102DI-02 ESD and Latch Up Test Results

Test	Test Conditions	Total Sample Size	Number of Failures	Reference Standard
Electrostatic Discharge Human Body Model	$T_A = 25^\circ C, +/-4kV$	10	0	JESD-A114
Electrostatic Discharge Charged Device Model	$T_A = 25^\circ C, +/-1kV$	10	0	JESD-C101
Latch Up	$T_A = 25^\circ C, +/-100mA, 1.27x OV$	10	0	JESD78
Latch Up	$T_A = 125^\circ C, +/-100mA, 1.27x OV$	10	0	JESD78

Note: ATE results are used to determine PASS/FAIL. Parametric shift < 10%.

